

## LL42 - LL43

### FEATURES :

- For general purpose applications.
- This diode features very low turn-on voltage and fast switching. This device is protected by a PN junction guard ring against excessive voltage, such as electrostatic discharges
- These diodes are also available in the DO-35 case with type designations BAT42 to BAT43
- Pb / RoHS Free

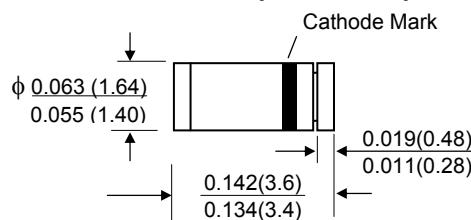
### MECHANICAL DATA :

**Case:** MiniMELF Glass Case (SOD-80C)

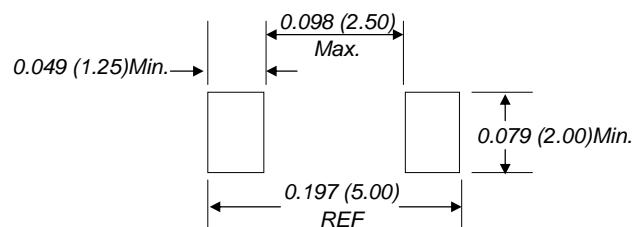
**Weight:** approx. 0.05g

### SCHOTTKY BARRIER DIODES

#### MiniMELF (SOD-80C)



#### Mounting Pad Layout



Dimensions in inches and ( millimeters )

### Maximum Ratings and Thermal Characteristics (Rating at 25 °C ambient temperature unless otherwise specified.)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	30	V
Continuous Forward Current	I <sub>F</sub>	200 <sup>(1)</sup>	mA
Repetitive Peak Forward Current at tp < 1s,	I <sub>FRM</sub>	500 <sup>(1)</sup>	mA
Forward Surge Current at tp < 10 ms,	I <sub>FSM</sub>	4 <sup>(1)</sup>	A
Power Dissipation ,Ta = 65 °C	P <sub>D</sub>	200 <sup>(1)</sup>	mW
Thermal Resistance Junction to Ambient Air	R <sub>θJA</sub>	300 <sup>(1)</sup>	°C/W
Junction Temperature	T <sub>J</sub>	125	°C
Ambient Operating Temperature Range	T <sub>a</sub>	-55 to + 125	°C
Storage temperature range	T <sub>s</sub>	-65 to + 150	°C

Note: (1) Valid provided that electrodes are kept at ambient temperature

### Electrical Characteristics (T<sub>J</sub> = 25 °C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Breakdown Voltage	V <sub>(BR)R</sub>	I <sub>R</sub> = 100 μA (pulsed)	30	-	-	V
Reverse Current	I <sub>R</sub>	V <sub>R</sub> = 25 V	-	-	1.0	μA
Pulse Test tp <300μs , δ <2%		V <sub>R</sub> = 25 V , T <sub>J</sub> = 100 °C	-	-	100	
Forward Voltage	LL42	I <sub>F</sub> = 200mA	-	-	1.00	
LL42	I <sub>F</sub> = 10mA	-	-	0.40		V
LL42	I <sub>F</sub> = 50mA	-	-	0.65		
LL43	I <sub>F</sub> = 2mA	0.26	-	0.33		
LL43	I <sub>F</sub> = 15mA	-	-	0.45		
Diode Capacitance	C <sub>d</sub>	V <sub>R</sub> = 1V, f = 1MHz	-	7	-	pF
Reverse Recovery Time	T <sub>rr</sub>	I <sub>F</sub> = 10mA, I <sub>R</sub> = 10mA , to I <sub>R</sub> = 1mA, R <sub>L</sub> = 100 Ω	-	-	5	ns